

# Daniel Becerra

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

17  
papers

258  
citations

10  
h-index

16  
g-index

17  
ext. papers

280  
ext. citations

2.5  
avg, IF

2.99  
L-index

#	Paper	IF	Citations
17	Semipolar III-nitride laser diodes for solid-state lighting <b>2019</b> ,		1
16	Efficient tunnel junction contacts for high-power semipolar III-nitride edge-emitting laser diodes. <i>Optics Express</i> , <b>2019</b> , 27, 8327-8334	3.3	12
15	Continuous-wave operation of a semipolar InGaN distributed-feedback blue laser diode with a first-order indium tin oxide surface grating. <i>Optics Letters</i> , <b>2019</b> , 44, 3106-3109	3	19
14	Semipolar InGaN blue laser diodes with a low optical loss and a high material gain obtained by suppression of carrier accumulation in the p-waveguide region. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 020902	1.4	9
13	Compensation effects of high oxygen levels in semipolar AlGaIn electron blocking layers and their mitigation via growth optimization. <i>Journal of Crystal Growth</i> , <b>2019</b> , 507, 118-123	1.6	6
12	Demonstration of enhanced continuous-wave operation of blue laser diodes on a semipolar 202° GaN substrate using indium-tin-oxide/thin-p-GaN cladding layers. <i>Optics Express</i> , <b>2018</b> , 26, 1564-1572	3.3	22
11	Influence of well width fluctuations on recombination properties in semipolar InGaIn quantum wells studied by time- and spatially-resolved near-field photoluminescence. <i>Optical Materials Express</i> , <b>2017</b> , 7, 3116	2.6	10
10	Chemically assisted ion beam etching of laser diode facets on nonpolar and semipolar orientations of GaN. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 075008	1.8	13
9	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202°) plane InGaIn/GaN quantum wells. <i>Optical Materials Express</i> , <b>2016</b> , 6, 39	2.6	5
8	CW operation of high-power blue laser diodes with polished facets on semi-polar GaN substrates. <i>Electronics Letters</i> , <b>2016</b> , 52, 2003-2005	1.1	7
7	Dynamic characteristics of 410 nm semipolar (202°) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 101104	3.4	26
6	Measurement and analysis of internal loss and injection efficiency for continuous-wave blue semipolar (202°) III-nitride laser diodes with chemically assisted ion beam etched facets. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 091106	3.4	18
5	Effects of active region design on gain and carrier injection and transport of CW semipolar InGaIn laser diodes. <i>Applied Physics Express</i> , <b>2016</b> , 9, 092104	2.4	6
4	Continuous-wave operation of a semipolar InGaIn laser diode with a photoelectrochemically etched current aperture. <i>Applied Physics Express</i> , <b>2015</b> , 8, 042701	2.4	9
3	Impact of carrier localization on radiative recombination times in semipolar (202°) plane InGaIn/GaN quantum wells. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 211109	3.4	20
2	High spatial uniformity of photoluminescence spectra in semipolar (202°) plane InGaIn/GaN quantum wells. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 023111	2.5	25
1	High-power low-droop violet semipolar (303°) InGaIn/GaN light-emitting diodes with thick active layer design. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 171106	3.4	50

